

## ABSTRACT

Provided is a titanium sputtering target having a recrystallized structure having an average crystal grain diameter of 1  $\mu\text{m}$  or less. Also provided is a method for producing a titanium sputtering target, the method comprising the steps of: subjecting a cut titanium ingot to large strain processing to provide a processed sheet; subjecting the processed sheet to cold rolling at a rolling ratio of 30% or more to provide a rolled sheet; and subjecting the rolled sheet to a heat treatment at a temperature of 320 °C or less.